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## FET BIAS CONTROLLER

**ZNBG3000**  
**ZNBG3001**

**ISSUE 1- AUGUST 1998**

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### DEVICE DESCRIPTION

The ZNBG series of devices are designed to meet the bias requirements of GaAs and HEMT FETs commonly used in satellite receiver LNBS, PMR, cellular telephones etc. with a minimum of external components.

With the addition of two capacitors and a resistor the devices provide drain voltage and current control for 3 external grounded source FETs, generating the regulated negative rail required for FET gate biasing whilst operating from a single supply. This negative bias, at -3 volts, can also be used to supply other external circuits.

The ZNBG3000/1 contains three bias stages. A single resistor allows FET drain current to be set to the desired level. The series also offers the choice of drain voltage to be set for the FETs, the ZNBG3000 gives 2.2 volts drain whilst the ZNBG3001 gives 2 volts.

These devices are unconditionally stable over the full working temperature with the FETs in place, subject to the inclusion of the recommended gate and drain capacitors. These ensure RF stability and minimal injected noise.

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It is possible to use less than the devices full complement of FET bias controls, unused drain and gate connections can be left open circuit without affecting operation of the remaining bias circuits.

In order to protect the external FETs the circuits have been designed to ensure that, under any conditions including power up/down transients, the gate drive from the bias circuits cannot exceed the range -3.5V to 0.7V. Furthermore if the negative rail experiences a fault condition, such as overload or short circuit, the drain supply to the FETs will shut down avoiding excessive current flow.

The ZNBG3000/1 are available in QSOP16 packages for the minimum in devices size. Device operating temperature is -40 to 70°C to suit a wide range of environmental conditions.

### FEATURES

- Provides bias for GaAs and HEMT FETs
- Drives up to three FETs
- Dynamic FET protection
- Drain current set by external resistor
- Regulated negative rail generator requires only 2 external capacitors
- Choice in drain voltage
- Wide supply voltage range
- QSOP surface mount package

### APPLICATIONS

- Satellite receiver LNBS
- Private mobile radio (PMR)
- Cellular telephones
- Single in single out C Band LNB

## ZNBG3000

## ZNBG3001

**ABSOLUTE MAXIMUM RATINGS**

Supply Voltage	-0.6V to 15V	<b>Power Dissipation (T<sub>amb</sub>= 25°C)</b>	
Supply Current	100mA	QSOP16	500mW
Drain Current (per FET) (set by R <sub>CAL1</sub> and R <sub>CAL2</sub> )	0 to 15mA		
Output Current	100mA		
Operating Temperature	-30 to 70°C		
Storage Temperature	-40 to 85°C		

**ELECTRICAL CHARACTERISTICS TEST CONDITIONS (Unless otherwise stated):**  
 T<sub>amb</sub>= 25°C, V<sub>CC</sub>=5V, I<sub>D</sub>=10mA (R<sub>CAL1</sub>=33kΩ)

SYMBOL	PARAMETER	CONDITIONS	LIMITS			UNITS
			Min	Typ	Max	
V <sub>CC</sub>	Supply Voltage		5		12	V
I <sub>CC</sub>	Supply Current	I <sub>D1</sub> to I <sub>D3</sub> =0 I <sub>D1</sub> to I <sub>D3</sub> =10mA			10 40	mA mA
V <sub>SUB</sub>	Substrate Voltage (Internally generated)	I <sub>SUB</sub> = 0 I <sub>SUB</sub> = -200μA	-3.5	-2.8	-2 -2	V V
E <sub>ND</sub> E <sub>NG</sub>	Output Noise Drain Voltage Gate Voltage	C <sub>G</sub> =4.7nF, C <sub>D</sub> =10nF C <sub>G</sub> =4.7nF, C <sub>D</sub> =10nF			0.02 0.005	V <sub>pkpk</sub> V <sub>pkpk</sub>
f <sub>O</sub>	Oscillator Freq.		200	330	800	kHz

**DRAIN CHARACTERISTICS**

I <sub>DO</sub>	Output Current Range	Set by R <sub>CAL1</sub>	0		15	mA
I <sub>D</sub>	Current		8	10	12	mA
ΔI <sub>DV</sub>	Current Change with V <sub>CC</sub>	V <sub>CC</sub> =5 to 12V		0.5		%/V
ΔI <sub>DT</sub>	with T <sub>j</sub>	T <sub>j</sub> =-30 to +70°C		0.05		%/°C
V <sub>D</sub>	Voltage	ZNBG3000 ZNBG3001 I <sub>D1</sub> to I <sub>D3</sub> =10mA	2 1.8	2.2 2	2.4 2.2	V V
ΔV <sub>DV</sub>	Voltage Change with V <sub>CC</sub>	V <sub>CC</sub> = 5 to 12V		0.5		%/V
ΔV <sub>DT</sub>	with T <sub>j</sub>	T <sub>j</sub> = -30 to +70°C		50		ppm

<b>ZNBG3000</b> <b>ZNBG3001</b>
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SYMBOL	PARAMETER	CONDITIONS	LIMITS			UNITS
			Min	Typ	Max	

**GATE CHARACTERISTICS**

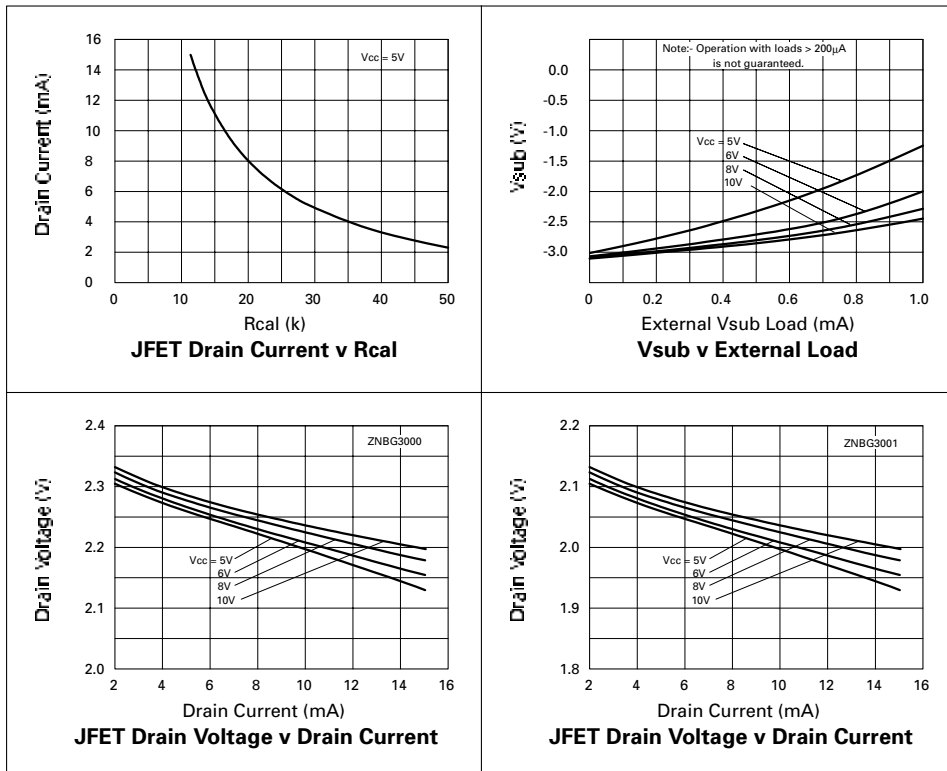
$I_{GO}$	Output Current Range		-30		2000	$\mu A$
$V_{OL}$	Output Voltage Output Low	$I_{D1}$ to $I_{D3}=12mA$ $I_{G1}$ to $I_{G3}=0$	-3.5		-2	V
		$I_{D1}$ to $I_{D3}=12mA$ $I_{G1}$ to $I_{G3}= -10\mu A$	-3.5		-2	V
$V_{OH}$	Output High	$I_{D1}$ to $I_{D3}= 8mA$ $I_{G1}$ to $I_{G3}= 0$	0.4		1	V

Notes:

- The negative bias voltages specified are generated on-chip using an internal oscillator. Two external capacitors,  $C_{NB}$  and  $C_{SUB}$ , of 47nF are required for this purpose.
- The characteristics are measured using an external reference resistors  $R_{CAL1}$  of value 33k $\Omega$  wired from pin  $R_{CAL1}$  to ground.
- Noise voltage is not measured in production.
- Noise voltage measurement is made with FETs and gate and drain capacitors in place on all outputs.  $C_G$ , 4.7nF, are connected between gate outputs and ground,  $C_D$ , 10nF, are connected between drain outputs and ground.

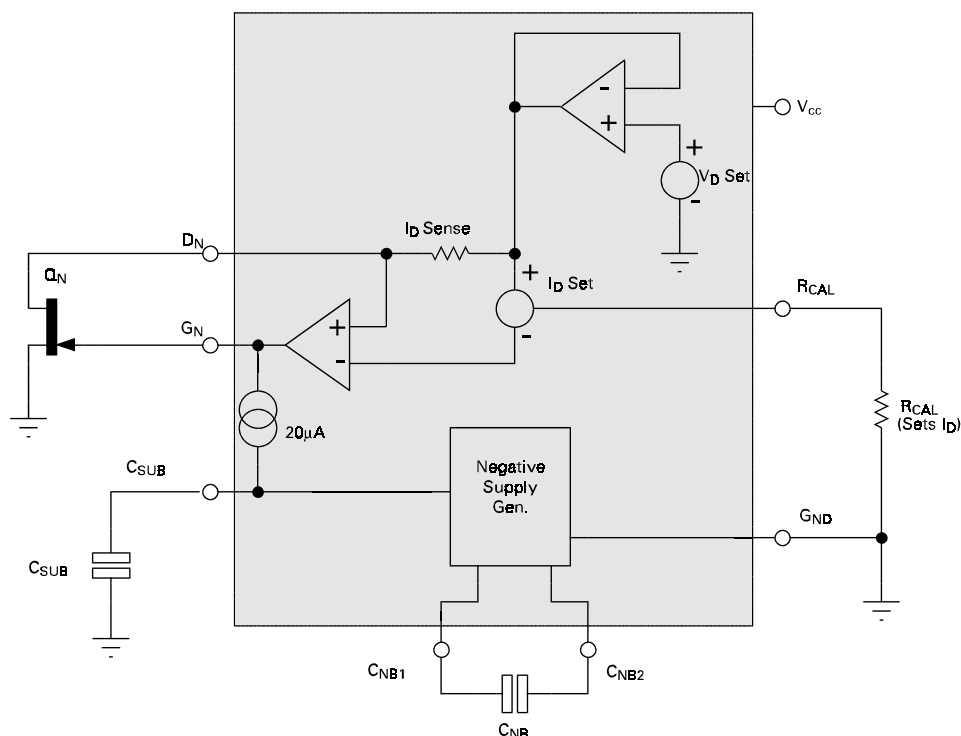
**ZNBG3000**  
**ZNBG3001**

**TYPICAL CHARACTERISTICS**



**ZNBG3000  
ZNBG3001**

**FUNCTIONAL DIAGRAM**



**FUNCTIONAL DESCRIPTION**

The ZNBG devices provide all the bias requirements for external FETs, including the generation of the negative supply required for gate biasing, from the single supply voltage.

The diagram above shows a single stage from the ZNBG series. The ZNBG3000/1 contains 3 such stages.

The drain voltage of the external FET  $Q_N$  is set by the ZNBG device to its normal operating voltage. This is determined by the on board  $V_D$  Set reference, for the ZNBG3000 this is nominally 2.2 volts whilst the ZNBG3001 provides nominally 2 volts.

The drain current taken by the FET is monitored by the low value resistor  $I_D$  Sense. The amplifier driving the gate of the FET adjusts the gate voltage of  $Q_N$  so that the drain current taken matches the current called for by an external resistor  $R_{CAL}$ . Both ZNBG devices have the facility to program different drain currents into selected FETs.

Since the FET is a depletion mode transistor, it is usually necessary to drive its gate negative with respect to ground to obtain the required drain current. To provide this capability powered from a single positive supply, the device includes a low current negative supply generator. This generator uses an internal oscillator and two external capacitors,  $C_{NB}$  and  $C_{SUB}$ .



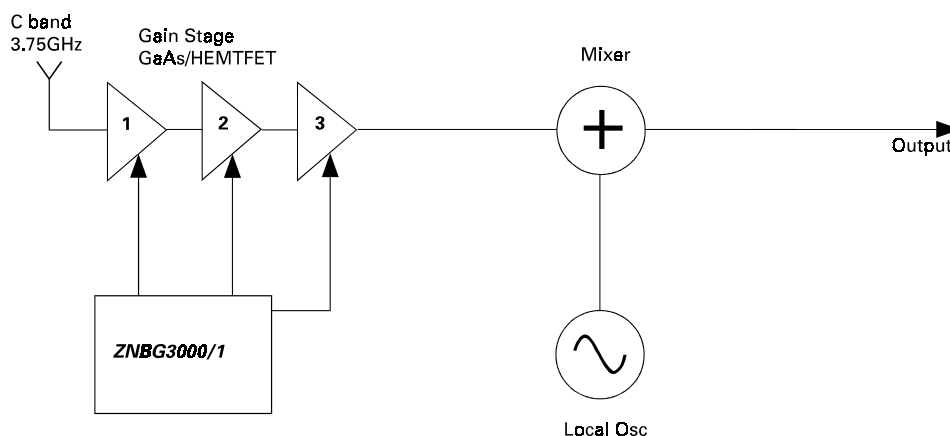
**ZNBG3000**  
**ZNBG3001**

**APPLICATIONS INFORMATION (Continued)**

The ZNBG devices have been designed to protect the external FETs from adverse operating conditions. With a JFET connected to any bias circuit, the gate output voltage of the bias circuit can not exceed the range -3.5V to 0.7V, under any conditions including powerup and powerdown transients. Should the negative bias generator be shorted or overloaded so that the drain current of the external FETs can no longer be controlled, the drain supply to FETs is shut down to avoid damage to the FETs by excessive drain current.

The following diagram show the ZNBG3000/1 in typical LNB applications.

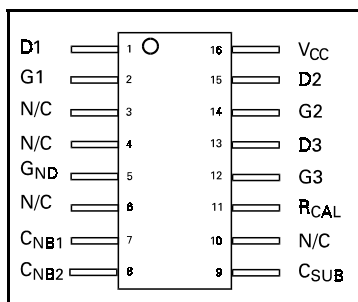
**Single in/Single out C band LNB block diagram**





**ZNBG3000**  
**ZNBG3001**

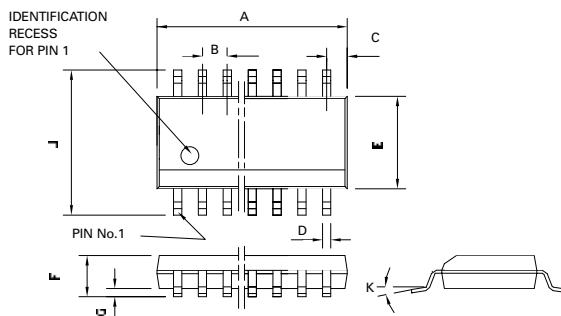
**CONNECTION DIAGRAMS**



**ORDERING INFORMATION**

Part Number	Package	Part Mark
ZNBG3000Q16	QSOP16	ZNBG3000
ZNBG3001Q16	QSOP16	ZNBG3001

**PACKAGE DIMENSIONS**



PIN	Millimetres		Inches	
	MIN	MAX	MIN	MAX
A	4.80	4.90	0.033	0.039
B	0.635		0.025 NOM	
C	0.177	0.267	0.007	0.011
D	0.20	0.30	0.008	0.012

E	3.81	3.99	0.15	0.157
F	1.35	1.75	0.053	0.069
G	0.10	0.25	0.004	0.01
J	5.79	6.20	0.228	0.244
K	0°	8°	0°	8°



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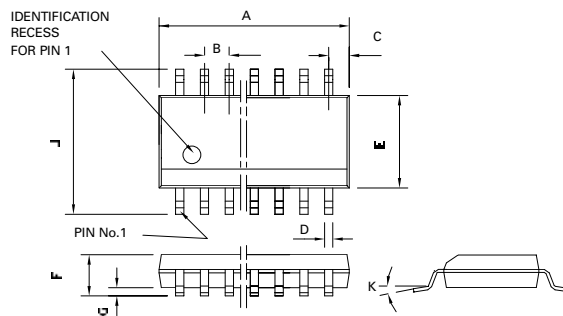
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**ZNBG4000 ZNBG4001  
 ZNBG6000 ZNBG6001**

**ZNBG3000  
 ZNBG3001**

**PACKAGE DIMENSIONS**



PIN	Millimetres		Inches	
	MIN	MAX	MIN	MAX
A	4.80	4.90	0.033	0.039
B	0.635		0.025 NOM	
C	0.177	0.267	0.007	0.011
D	0.20	0.30	0.008	0.012

E	3.81	3.99	0.15	0.157
F	1.35	1.75	0.053	0.069
G	0.10	0.25	0.004	0.01
J	5.79	6.20	0.228	0.244
K	0°	8°	0°	8°

